

PEMD30; PUMD30

NPN/PNP double resistor-equipped transistors;
R1 = 2.2 k Ω , R2 = open

Rev. 01 — 31 March 2006

Product data sheet

1. Product profile

1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		PNP/PNP complement	NPN/PNP complement
	Philips	JEITA		
PEMD30	SOT666	-	PEMB30	PEMH30
PUMD30	SOT363	SC-88	PUMB30	PUMH30

1.2 Features

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Cost-saving alternative for BC847BPN and BC847BVN
- Switching loads

1.4 Quick reference data

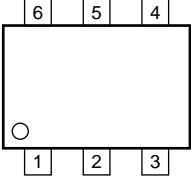
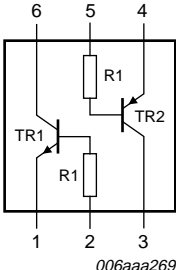
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω

PHILIPS

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1	 <p>001aab555</p>	 <p>006aaa269</p>
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
PEMD30	-	plastic surface-mounted package; 6 leads	SOT666
PUMD30	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMD30	2U
PUMD30	*B3

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
Per transistor; for the PNP transistor with negative polarity						
V _{CBO}	collector-base voltage	open emitter	-	50	V	
V _{CEO}	collector-emitter voltage	open base	-	50	V	
V _{EBO}	emitter-base voltage	open collector	-	5	V	
I _O	output current		-	100	mA	
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	100	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	SOT363		[1]	-	200	mW
	SOT666		[1][2]	-	200	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	SOT363		[1]	-	300	mW
	SOT666		[1][2]	-	300	mW
T _{stg}	storage temperature		-65	+150	°C	
T _j	junction temperature		-	150	°C	
T _{amb}	ambient temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Per transistor							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	SOT363		[1]	-	-	625	K/W
	SOT666		[1][2]	-	-	625	K/W
Per device							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	SOT363		[1]	-	-	416	K/W
	SOT666		[1][2]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

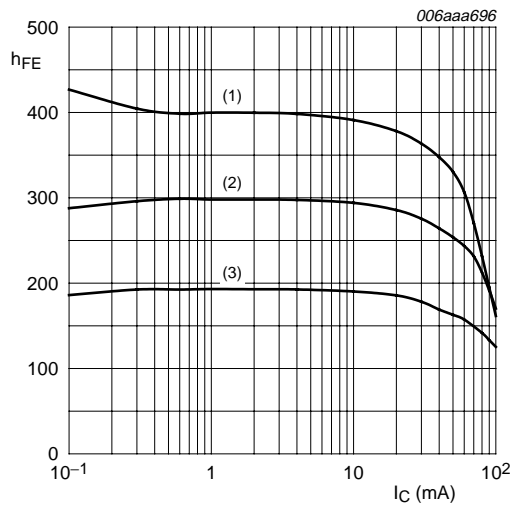
[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified.

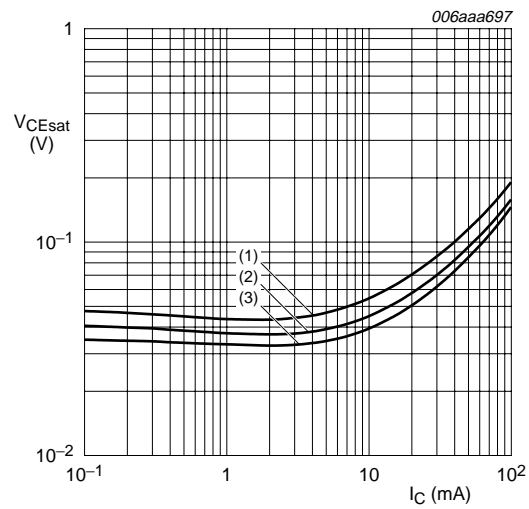
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
I_{CBO}	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	-	-	1	μA
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150^\circ\text{C}$	-	-	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 20\text{ mA}$	30	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$				
		TR1 (NPN)	-	-	2.5	pF
		TR2 (PNP)	-	-	3	pF



$V_{CE} = 5 \text{ V}$

- (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

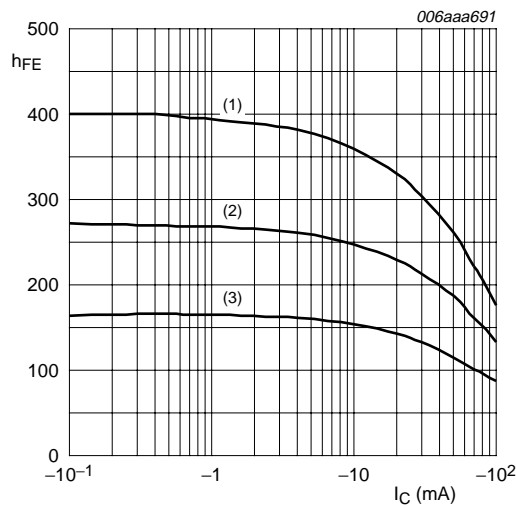
Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



$I_C/I_B = 20$

- (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

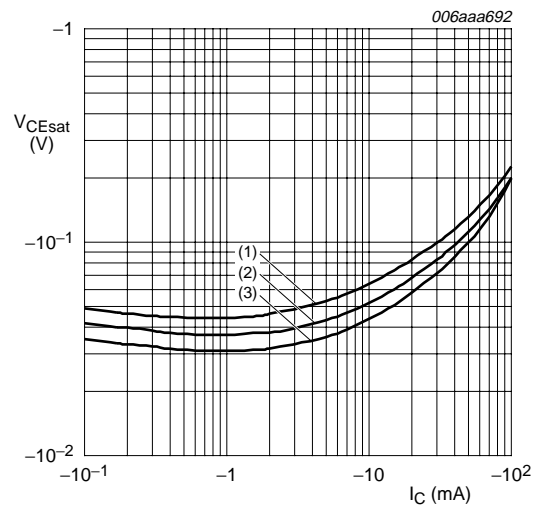
Fig 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = -5 \text{ V}$

- (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 3. TR2 (PNP): DC current gain as a function of collector current; typical values



$I_C/I_B = 20$

- (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 4. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

8. Package outline

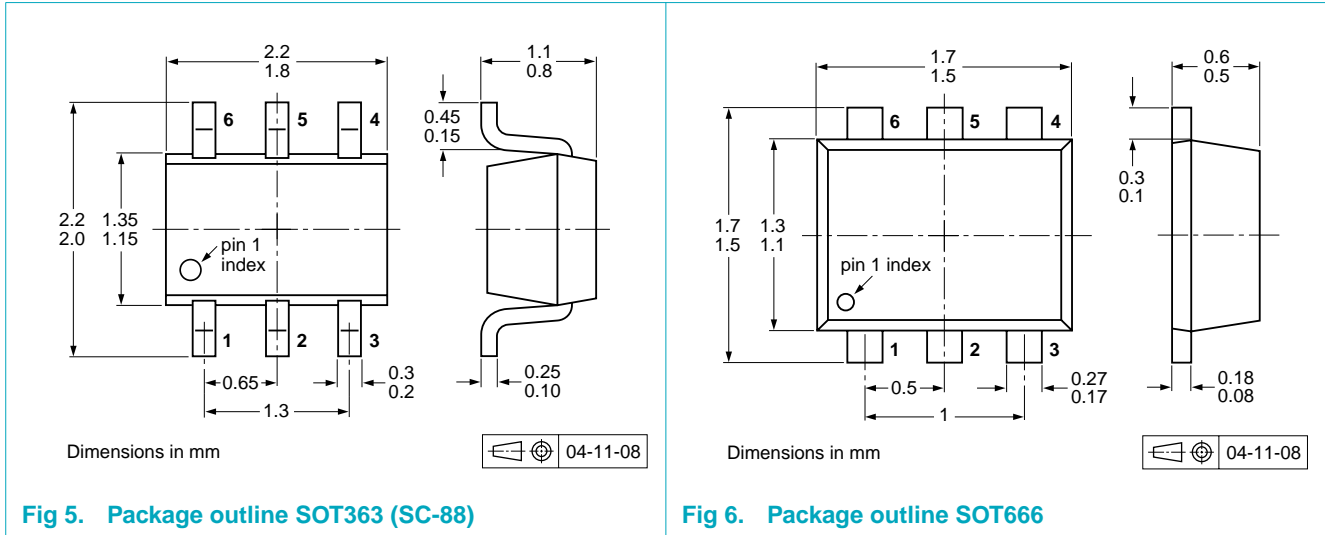


Fig 5. Package outline SOT363 (SC-88)

Fig 6. Package outline SOT666

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

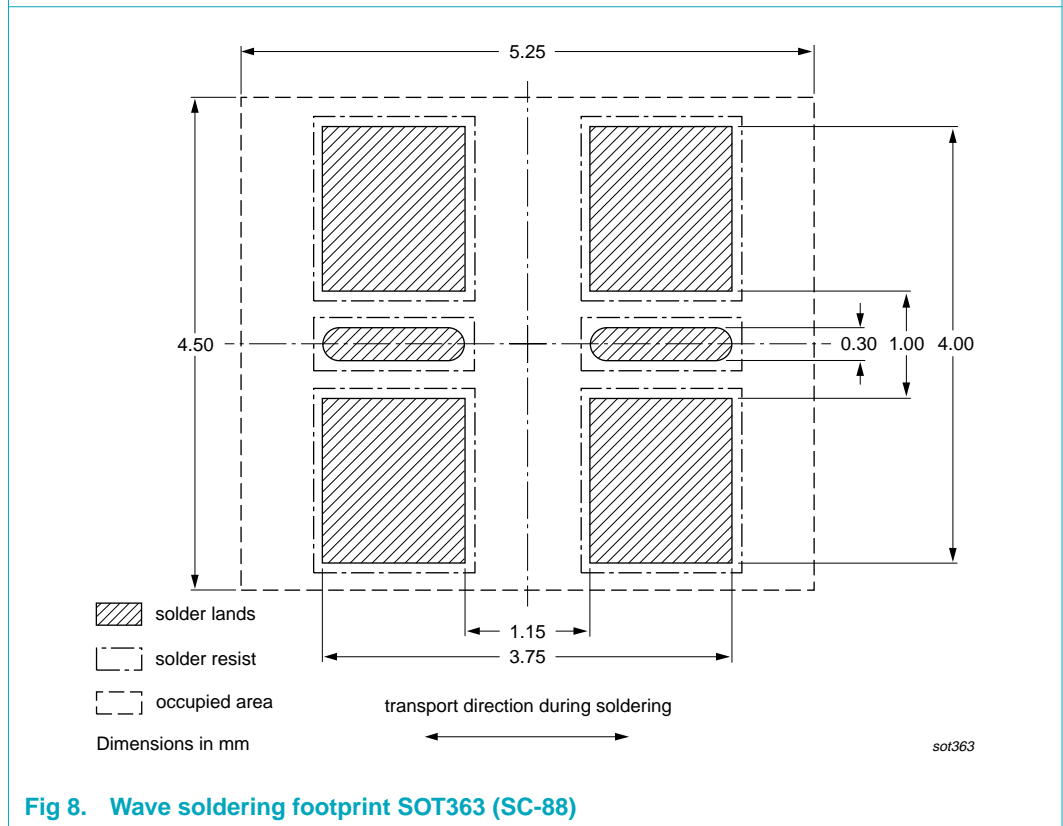
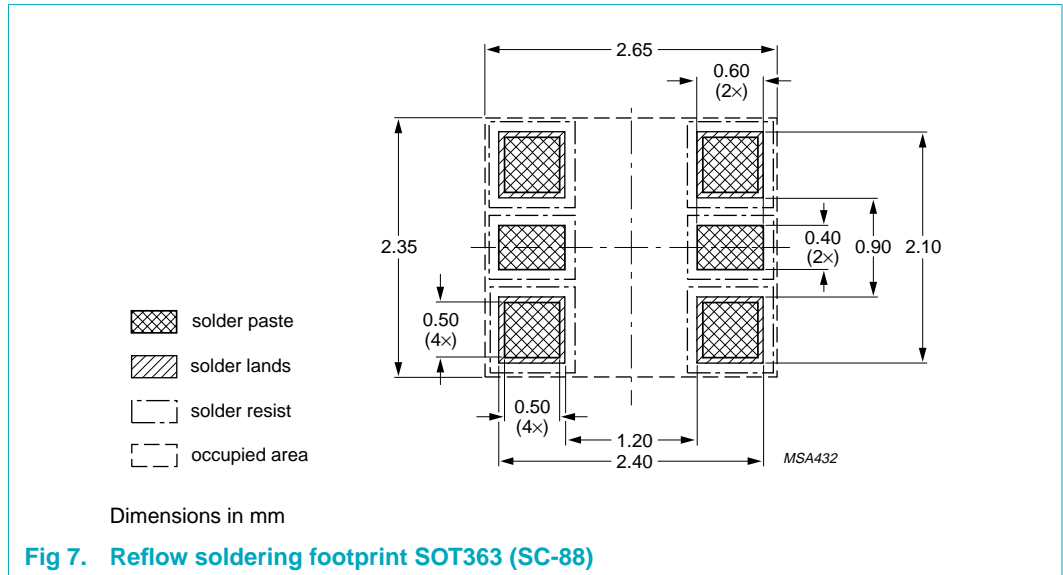
Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMD30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMD30	SOT363	4 mm pitch, 8 mm tape and reel; T1 ^[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 ^[3]	-125	-	-	-165

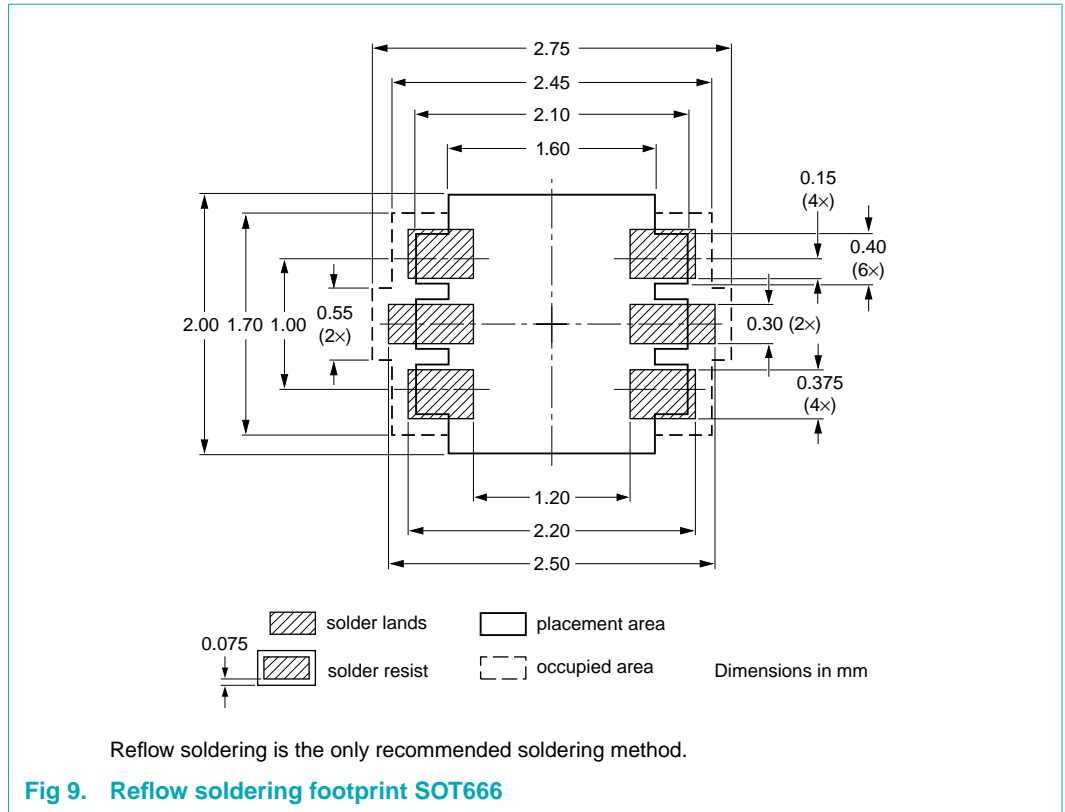
[1] For further information and the availability of packing methods, see [Section 13](#).

[2] T1: normal taping

[3] T2: reverse taping

10. Soldering





11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD30_PUMD30_1	20060331	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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